EAST - [10696040.wsp:1]

File View Edit Tools Window Help

- Drafts
  - BRS: 31 and (
  - BRS: 36
- Pending
- Active
  - L35: (1290) (base and drain and source and emitter
  - L36: (132) 35 and (concentration with constant)
  - L37: (10) (US-6060731-$ or US-6501128-$ or US-55369
  - L38: (129) 36 not 37
  - L39: (93) 38 and (collector and gate and (insulat$4
  - L40: (69) 39 and (impurity adj concentration)
  - L41: (68) 40 and electrode
  - L42: (48) 41 and (trench or buried)
- Failed
- Saved
  - (1) "20040089886"
  - (2) "6670658"
  - (5) "6495871"
  - (21) Hattori-hidetaka.in.
  - (0) 6670658.URPN.
  - (9266) ("IGBT" or (insulat$3 adj gate adj bibolar a
  - (38) ("IGBT" or (insulat$3 adj gate adj bibolar adj
  - (48) ("IGBT" or (insulat$3 adj gate adj bibolar adj
  - (38) (("IGBT" or (insulat$3 adj gate adj bibolar ad

Browse | Queue | Clear

DBs: USPAT,US-PGPUB,EPO,JPO,IBM_TDB | Plurals

Default operator: OR | Highlight all hit terms initially

41 and (trench or buried)

BRS form | IBAR form | Image | Text | HTML

	U	1	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current
1	☐	☐	☐	☐	US 20040166637	20040826	33	Manufacturing method of semiconductor device	438/270	257/E21.9;
2	☐	☐	☐	☐	US 20040089886	20040513	NA	Power semiconductor element capable of improving short circuit withstand capability while maintaining low on-voltage and method of	257/279	257/E21.4;
3	☐	☐	☐	☐	US 20040061518	20040401	88	Time limit function utilization	324/765	324/464
4	☐	☐	☐	☐	US 20030205820	20031106	41	Semiconductor device and method of manufacturing the same	257/770	257/768; 257/773;
5	☐	☐	☐	☐	US 20030190788	20031009	25	Semiconductor device and its manufacturing method	438/285	257/E21.3;
6	☐	☐	☐	☐	US 20030146473	20030807	25	Semiconductor device	257/346	257/E29.6;
7	☐	☐	☐	☐	US 20030089966	20030515	65	Power semiconductor element capable of improving short circuit withstand capability while maintaining low on-voltage and method of	257/565	257/E21.4;
8	☐	☐	☐	☐	US 20030042537	20030306	76	Semiconductor device	257/328	257/329; 257/330;
9	☐	☐	☐	☐	US 20030034520	20030220	58	Semiconductor device having gate electrode in which depletion layer can be generated	257/344	257/402; 257/408;
10	☐	☐	☐	☐	US	20021024	58	SEMICONDUCTOR DEVICE	257/368	257/E21.

Hits | Details | HTML

Ready

NUM